2N3767SMD



MECHANICAL DATA Dimensions in mm (inches)



NPN BIPOLAR TRANSISTOR IN A CERAMIC SURFACE MOUNT PACKAGE FOR HIGH REL APPLICATIONS

FEATURES

- HIGH VOLTAGE
- FAST SWITCHING
- CERAMIC SURFACE MOUNT PACKAGE
- SCREENING OPTIONS AVAILABLE

SMD1 (TO-276AB)

Underside View

PIN 1 – Base PIN 2 – Collector PIN 3 – Emitter

ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C unless otherwise stated)

V _{CBO}	Collector– Base Voltage (I _E = 0)	100V			
V _{CEO}	Collector– Emitter Voltage (I _B = 0)	80V			
V _{EBO}	Emiiter– Base Voltage (I _B = 0)	6V			
I _B	Base Current	2A			
I _C	Collector Current	4A			
T _J ,T _{STG}	Operating and Storage Junction Temperature Range	–55 to +150°C			
P _D	Total Device Dissipation @ $T_C = 25^{\circ}C$	25W			
	Derate above 25°C	5°C/W			

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.



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ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise stated)

	Parameter	Test Conditions		Min.	Тур.	Max.	Unit			
	OFF CHARACTERISTICS									
V _{(BR)CEO}	Collector Emitter Breakdown Voltage ¹	I _C = 100mA	I _B = 0	80			V			
		V _{CE} = 100V	$V_{BE} = 1.5V$			100	μΑ			
I _{CEX}	Collector Cutoff Current	V _{CE} = 70V	$V_{BE} = 1.5V$			1.0				
			$T_A = 150^{\circ}C$							
I _{EBO}	Emitter Base Cutoff Current	$V_{EB} = 6V$	$I_{\rm C} = 0$			0.75	mA			
I _{CEO}	Collector Emitter Cutoff Current	$V_{CE} = 80V$	I _B = 0			0.7				
I _{CBO}	Collector Base Cutoff Current	V _{CB} = 100V	I _E = 0			0.1				
	ON CHARACTERISTICS									
h _{FE}	DC Current Gain	I _C = 50mA	$V_{CE} = 5V$	30			_			
		I _C = 500mA	$V_{CE} = 5V$	40		160				
		I _C = 1.0A	V _{CE} = 10V	20						
V _{CE(sat)}	Collector Emitter Saturation Voltage	I _C = 1.0A	I _B = 0.1A			2.5	V			
V _{BE}	Base Emitter Voltage	I _C = 1.0A	V _{CE} = 10V			1.5				
	TRANSIENT CHARACTERISTICS									
f _T	Transistion Frequency	$V_{CE} = 10V$	I _C = 500mA			10	MHz			
			f = 10MHz							
C _{OB}	Common Base Output Capacitance	V _{CB} = 10V	$I_{\rm C} = 0$ A			50	pF			
			f = 100KHz							
h _{fe}	Small Signal Current Gain	V _{CE} = 10V	I _C = 100mA	40						
			f = 1.0kHz	40			-			

1) Pulse test : Pulse Width < 100μ s ,Duty Cycle <1%

2) f_t is defined as the frequency at which $|h_{fe}|$ extrapolates to untity.

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